

Hitachi Power Diode

Status List

Date: Feb. 2017

Compliance status of RoHS directive

C:Compliant S.C:Compliant (Included RoHS exemption substance) N:Non compliant

Production Status

M:Mass production O:Order production W:Working sample D:Discontinued

General-Use Rectifier Diodes

◆Glass Molded Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	status	
	V _{RRM} (V)	I _{F(AV)} (A)	I _{FSM} (A)	T _j (°C)	V _{FM} (at I _{FM}) (V) (A)	t _{rr} (ms)				
H14A	100	1.0	45	-40 ~+175	1.0 (1.0)	-	2A	S.C	M	
B	200									
C	300									
D	400									
E	500									
F	600									
H	800									
J	1,000			-40 ~+165						
V06C	200	1.1	35	-65 ~+175	1.4 (1.1)	-	2A	S.C	M	
E	400									
G	600									
J	800									
V03C	200	1.3	40		-65 ~+175	1.1 (1.3)	-	2A	S.C	M
E	400									
G	600									
J	800									
U05B	100	2.5	100	-65 ~+175		1.1 (2.5)	-	2B	S.C	M
C	200									
E	400									
G	600									
J	800									
U15B	100	3	80		-65 ~+175	1.0 (3.0)	-	2B	S.C	M
C	200									
E	400									
G	600		60							
J	800									

◆Resin Molded Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	status
	V _{RRM} (V)	I _{F(AV)} (A)	I _{FSM} (A)	T _j (°C)	V _{FM} (at I _{FM}) (V) (A)	t _{rr} (ms)			
DSA3A1	100	3.0	120	-40~+150	1.0 (3.0)	-	2C	S.C	M
2	200								
4	400								

◆Surface Mount Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	status
	V _{RRM} (V)	I _{F(AV)} (A)	I _{FSM} (A)	T _j (°C)	V _{FM} (at I _{FM}) (V) (A)	t _{rr} (ms)			
DSM1MA1	100	1.0	25	-40 ~+150	1.1 (1.0)	-	4A	S.C	M
2	200								
4	400								
DSM3MA1	100	3.0	80	-40 ~+150	1.0 (3.0)	-	4B	S.C	M
2	200								
4	400								

Fast Recovery Diodes

◆Glass Molded Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	status		
	VRRM (V)	IF(AV) (A)	IFSM (A)	Tj (°C)	VFM (at IFM) (V) (A)	trr (ms)					
DFG1E6	600	0.3	5	-65 ~+150	5.0 (0.3)	35ns	2A	S.C	M		
8	800										
10	1,000										
DFG1D1	100	1.0	30		-65 ~+150	1.5 (1.0)	50ns	2A	S.C	M	
2	200										
4	400										
DFG1C1	100	1.0	35			-65 ~+150	1.2 (1.0)	0.1	2A	S.C	M
2	200										
4	400		30				1.6 (1.0)				
6	600										
8	800										
DFG3A1	100	3.0	70	-65 ~+150			1.3 (3.0)	0.1	2B	S.C	M
2	200										
4	400										
V19B	100	1.0	30		-65 ~+150		1.2 (1.0)	0.2	2A	S.C	M
C	200										
E	400										
G	600										
DFG1A8	800	1.0	40			-65 ~+165	1.2 (1.0)	0.2	2A	S.C	M
H114B	200	1.0	40			-40 ~+150	1.15 (1.0)	0.2	2A	S.C	M
D	400										
E	500										
F	600										
U19B	100	2.5	80	-65 ~+150			1.3 (2.5)	0.2	2B	S.C	M
C	200										
E	400										
DFG2A6	600	2.5	80		-65 ~+165	1.3 (2.5)	0.2	2B	S.C	M	
8	800										
V11J	800	0.4	30	-65 ~+150		2.5 (0.4)	0.4	2A	S.C	M	
L	1,000										
M	1,300										
N	1,500										
V09C	200	0.8	35		-65 ~+165	1.6 (0.8)	0.4	2A	S.C	M	
E	400										
G	600										
U07J	800	1.0	50	-65 ~+140		2.5 (1.0)	0.4	2B	S.C	M	
L	1,000										
M	1,300										
N	1,500										
U06C	200	2.0	80		-65 ~+150	1.2 (2.0)	0.4	2B	S.C	M	
E	400										
G	600										

◆Surface Mount Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	status
	VRRM (V)	IF(AV) (A)	IFSM (A)	Tj (°C)	VFM (at IFM) (V) (A)	trr (ns)			
DFM1MF2	200	1.0	25	-40 ~+150	0.95 (1.0)	35	4A	S.C	M
DFM3MF2	200	3.0	50	-40 ~+150	0.95 (3.0)	35	4B	S.C	M

Controlled Avalanche Diodes

◆Glass Molded Type

Type	Absolute maximum ratings					Characteristics		Outline	RoHS Status	status
	VRRM (V)	IF(AV) (A)	PRM (W)	IFSM (A)	Tj (°C)	VFM (at IFM) (V) (A)				
H24F	600	1.0	1,000	45	-65 ~ +175	1.0 (1.0)	2A	S.C	M	
H	800				-65 ~ +165					
J	1,000									
V08E	400	1.1	40	35	-65 ~ +175	1.4 (1.1)	2A	S.C	M	
G	600									
J	800									
V07E	400	1.3	40	40	-65 ~ +175	1.1 (1.3)	2A	S.C	M	
G	600									
J	800									
V17A	50	1.3	1,500	50	-40 ~ +165	1.1 (1.3)	2A	S.C	M	
B	100									
C	200									
D	300									
E	400									
U17B	100	2.5	3,000	100	-40 ~ +175	1.1 (2.5)	2B	S.C	M	
C	200									
D	300									
E	400									

High Voltage – Fast Recovery Diodes

◆Resin Molded Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	status
	VRRM (kV)	* IF(AV) (mA)	IFSM (A)	Tj (°C)	VFM (at IFM) (V) (mA)	trr (ns)			
DHM3T30	3	3 [15.75]	0.5	-40 ~ +120	13 (5)	100	1B	S.C	M
DHM3P40	4				13 (5)	100	1B	S.C	M
DHM3G80	8				25 (5)	100	1F	S.C	M
DHM3J120	12				42 (5)	100	1G	S.C	M
DHM3C140	14				45 (5)	100	1H	S.C	M
DHM3FJ60	6	1 [63]	0.5	-40 ~ +120	22 (5)	70	1F	S.C	M
DHM3FG80	8	3 [15.75]			28 (5)	70	1F	S.C	M
DHM3UM80	8	1 [100] 3 [15.75]			23 (5)	40	1F	S.C	M

* [] : Frequency, unit (kHz)

High Voltage – Fast Recovery Diodes (For Automotive)

◆Resin Molded Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	status
	VRRM (kV)	IF(AV) (mA)	IFSM (A)	Tj (°C)	VFM (at IFM) (V) (mA)	trr (ns)			
DHM10A30	3.0	10	1	+150	8.4 (10)	-	1K	S.C	M
DHM30A10	1.0	30	3		2.0 (10)	-	1M	S.C	M
DHM30A20	2.0	30	3		5.0 (10)	-	1M	S.C	M
DHM30A25	2.5	30	3		5.0 (10)	-	1M	S.C	M
DHM30A30	3.0	30	3		6.0 (10)	-	1F	S.C	M
DHM30A40	4.0	30	3		10.0 (10)	-	1L	S.C	M

Zener Diodes

◆ Glass Molded Type

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	status
	P (W)	PRSM (Wp)	T _j (°C)	V _z (V)		Test Current (mA)			
				Min.	Max.				
AW01-06	1.0	80	-40 ~+150	5.2	6.8	60	2A	S.C	M
AW01/AU01-07	1.0/2.5	80/160	-40 ~+150 / -40 ~+165	6.2	7.9	25/65	2A/2B	S.C / S.C	M / M
08				7.7	8.7	25/65			
09				8.5	9.6	25/65			
10				9.4	10.6	25/65			
11				10.4	11.6	25/65			
12				11.4	12.7	25/65			
13				12.4	14.1	25/65			
15				13.5	15.6	15/40			
16				15.3	17.1	15/40			
18				16.8	19.1	15/40			
20				18.8	21.2	15/40			
22				20.8	23.3	15/40			
24				22.7	25.6	10/25			
27				25.1	28.9	10/25			
30				28.0	32.0	10/25			
33	31.0	35.0	10/25						
Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	status
Type	PRSM (kW)	V _{DC} (V)	T _j (°C)	V _z (V)		Test Current (mA)			
				Min.	Max.				
DAM1MA/3MA12	0.6/1.8	9	-40 ~+150	11.4	12.7	25/75	4A/4C	S.C	M
13		10		12.4	14.1	25/75			
15		11		13.5	15.6	25/75			
16		12		15.3	17.1	15/75			
18		13		16.8	19.1	15/45			
20		14		18.8	21.2	15/45			
22		16		20.8	23.3	15/45			
24		18		22.7	25.6	10/30			
27		20		25.1	28.9	10/30			
30		22		28.0	32.0	10/30			
33		24		31.0	35.0	10/30			
36		26		33.4	38.6	10/30			
39		28		36.1	41.9	10/20			
43		31		39.8	46.2	6/20			
47		34		43.3	50.7	6/20			
51		37		46.9	55.1	6/20			
68		49		61.2	74.8	4/10			
75		54		67.5	82.5	4/10			
82	59	73.8	90.2	3/10					

Surge Suppressor Diodes

◆ Surface Mount Type

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	status
	PPPM (kW)	VRM (V)	T _j (°C)	V _z (V)		Test Current (mA)			
				Min.	Max.				
DAM1MB/2MB/3MB12	0.6/1.2/1.8	9.7	-65 ~ +185	11.4	12.7	1	4A/4B/4C	S.C	M
13		10.5		12.4	14.1	1			
15		12.1		13.5	15.6	1			
16		12.9		15.3	17.1	1			
18		14.5		16.8	19.1	1			
20		16.2		18.8	21.2	1			
22		17.8		20.8	23.3	1			
24		19.4		22.7	25.6	1			
27		21.8		25.1	28.9	1			
30		24.3		28.0	32.0	1			
33		26.8		31.0	35.0	1			
36		29.1		33.4	38.6	1			
39		31.6		36.1	41.9	1			
43		34.8		39.8	46.2	1			
47		38.0		43.3	50.7	1			
51		41.3		46.9	55.1	1			
68		55.1		61.2	74.8	1			
75		60.7		67.5	82.5	1			
82		66.4		73.8	90.2	1			

Load Dump Surge Suppressor Diodes

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	status
	PRSM (kW)	V _{DC} (V)	T _j (°C)	V _z (V)		Test (mA)			
				Min.	Max.				
ZSH5MA27(※)	3.0kW 62A	18	-40 ~ +150	24.0	30.0	10	6A	S.C	M
ZSH5MA27(A)(※)									
ZSH5MA27(S)(※)									
ZSH5MC27(※)	3.2kW 65A	22		24.0	30.0	10	6A	S.C	M
ZSH5MC27(S)(※)									
ZSH5MAZ27	3.4kW 70A	22		24.0	30.0	10	6B	S.C	M
ZSH8MD27	5.7kW 130A								
ZSH8MD40	5.7kW 80A	32		36.0	44.0	10	6B	S.C	M
ZSH5MK27	3.4kW 70A	22		24.0	30.0	10	7B	S.C	M
ZSH5MT27C	3.4kW 70A								
ZSH5MT27(Z)	4.3kW 90A								
ZSH5MT40C	4.3kW 62A	32	36.0	44.0	10	7A	S.C	M	
ZSH5MT48C	4.3kW 50A	39	43.2	52.8	10				
ZSH5MT53C	4.3kW 45A	43	47.7	58.3	10				
ZSH5MV14	4.3kW 200A	11	13.0	15.0	10	5	S.C	M	
ZSH5MV27	4.3kW 100A	22	24.0	30.0	10				

** Please consider alternative new products as following.

ZSH5MA27/27(A)/27(S) --> ZSH5MAZ27,ZSH5MT serie,ZSH8MD27
 ZSH5MC27/27(S) --> ZSH5MAZ27,ZSH5MT serie,ZSH8MD27

Discontinued

◆Surge Suppressor Diodes

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	status
	PRSM (kW)	V _{DC} (V)	T _j (°C)	V _Z (V)		Test (mA)			
				Min.	Max.				
DAM1MA10	0.6	7	-40 ~+150	9.4	10.6	25	4A	S.C	D
DAM3MA10	1.8	7		9.4	10.6	75	4B	S.C	D
DAM1MA11	0.6	8		10.4	11.6	25	4A	S.C	D
DAM3MA11	1.8	8		10.4	11.6	75	4B	S.C	D

◆Resin Molded Type

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	status	
	PRSM (kW)	V _{DC} (V)	T _j (°C)	V _Z (V)		Test Current (mA)				
				Min.	Max.					
DAM1SA/1A10	0.6	7	-40 ~+150	9.4	10.6	25	1A/1B	S.C / S.C	D / D	
11				8	10.4	11.6				25
12				9	11.4	12.7				25
13				10	12.4	14.1				25
15				11	13.5	15.6				25
16				12	15.3	17.1				15
18				13	16.8	19.1				15
20				14	18.8	21.2				15
22				16	20.8	23.3				15
24				18	22.7	25.6				10
27				20	25.1	28.9				10
30				22	28.0	32.0				10
33				24	31.0	35.0				10
36				26	33.4	38.6				10
39				28	36.1	41.9				10
43				31	39.8	46.2				6
47				34	43.3	50.7				6
51	37	46.9	55.1	6						
DAM3A/3B10	1.8	7	-40 ~+150	9.4	10.6	75	1E/1D	S.C / S.C	D / D	
11				8	10.4	11.6				75
12				9	11.4	12.7				75
13				10	12.4	14.1				75
15				11	13.5	15.6				75
16				12	15.3	17.1				75
18				13	16.8	19.1				45
20				14	18.8	21.2				45
22				16	20.8	23.3				45
24				18	22.7	25.6				30
27				20	25.1	28.9				30
30				22	28.0	32.0				30
33				24	31.0	35.0				30
36				26	33.4	38.6				30
39				28	36.1	41.9				30
43				31	39.8	46.2				20
47				34	43.3	50.7				20
51	37	46.9	55.1	20						

◆High Voltage – Fast Recovery Diodes

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	status
	V _{RRM} (kV)	* I _{F(AV)} (mA)	I _{FSM} (A)	T _j (°C)	V _{FM} (at I _{FM}) (V)	t _{rr} (ns)			
DHM3S20	2	3 [15.75]	0.5	-40 ~+120	10 (5)	100	1B	S.C	D
DHM3UG120	12	1 [100] 3 [15.75]			36 (5)	40	1G	S.C	D

*[]: Frequency, unit (kHz)

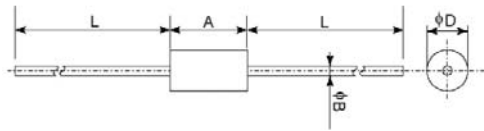
◆Load Dump Surge Suppressor Diodes

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	status
	PRSM (kW)	V _{DC} (V)	T _j (°C)	V _Z (V)		I _Z (mA)			
				Min.	Max.				
ZSA5A27	3.0kW	62A	-40 ~+150	24.0	30.0	10	3A	S.C	D
ZSA5MA27								3B	S.C

Outline

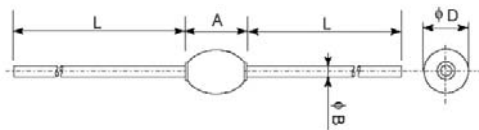
[Dimensions in mm]

● Outline No.1



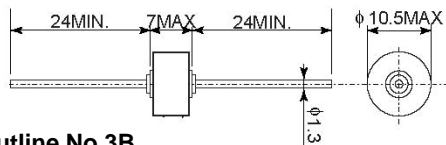
Items	A	φD	φB	L (Min.)
1A	3	2.5	0.6	28
1B	5	2.65	0.6	27
1C	5	2.65	0.8	27
1D	6	3.6	0.8	26
1E	7.5	6.4	1.2	26
1F	6.5	2.5	0.5	28
1G	10	2.5	0.5	26
1H	10	3	0.6	26,28
1J	8	3	0.6	28
1K	6.5	2.5	0.5	27
1L	8	3	0.6	27
1M	5	2.5	0.5	27

● Outline No.2

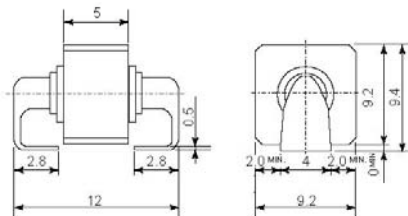


Items	A (Max.)	φD (Max.)	φB	L (Min.)
2A	5	3.5	0.8	29
2B	7	5	1.2	28
2C	7	5	1.2	27

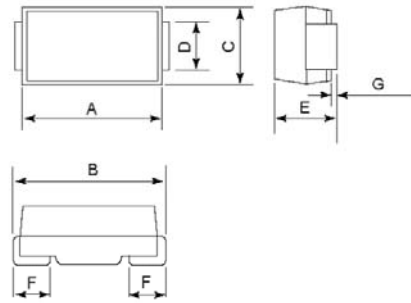
● Outline No.3A



● Outline No.3B

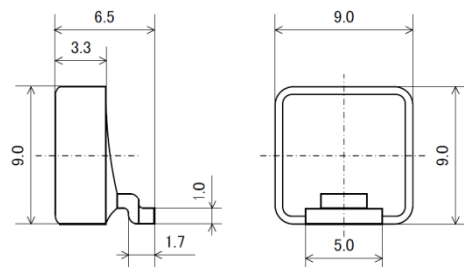


● Outline No.4



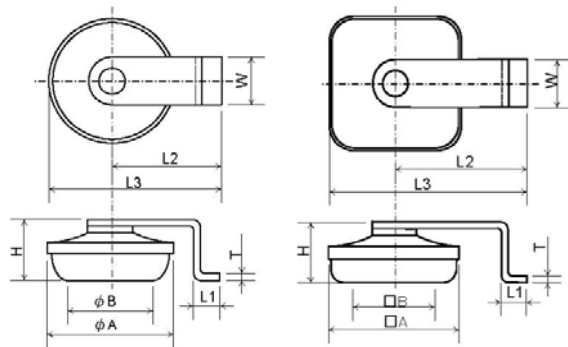
Items	A	B	C	D	E	F	G
4A	4.3	4.7	2.5	1.5	2.0	1.2	0.1
4B	4.4	5.4	3.6	2.0	2.3	1.2	0.2
4C	7.0	7.6	4.0	2.0	2.5	1.4	0.2

● Outline No.5



● Outline No.6

● Outline No.7A, 7B



Items	A	B	L1	L2	L3	H	W	T
6A	9.6	7.4	2.0	8.3	13.1	4.4	3.5	0.5
6B*	9.6	-	2.0	8.3	13.1	6.0	3.5	0.5
7A	10.0	7.5	2.0	10.0	15.0	4.4	3.5	0.5
7B**	10.0	7.5	2.0	10.0	15.0	4.4	2.7	0.5

*: Packages is different

** : JEDEC DO-218AB Compatible

Notices

1. The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact Hitachi Power Semiconductor Device (HPSD) sales department for the latest version of data sheets.
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